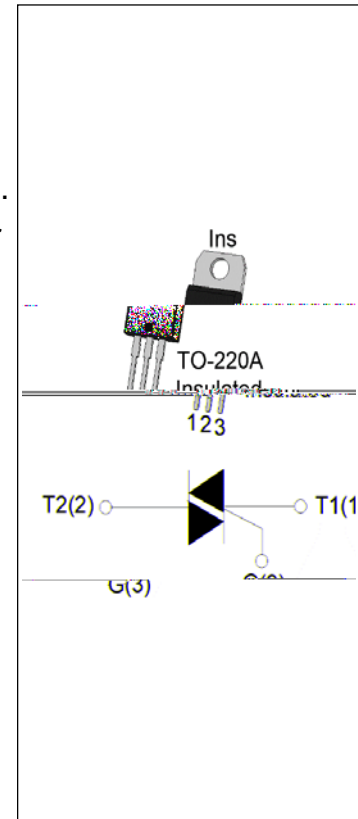


**JST12A-600BW 12A TRIAC**

Rev.A.1.0

The JST12A-600BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST12A-600BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST12A-600BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT} / /$	50/50/50	mA

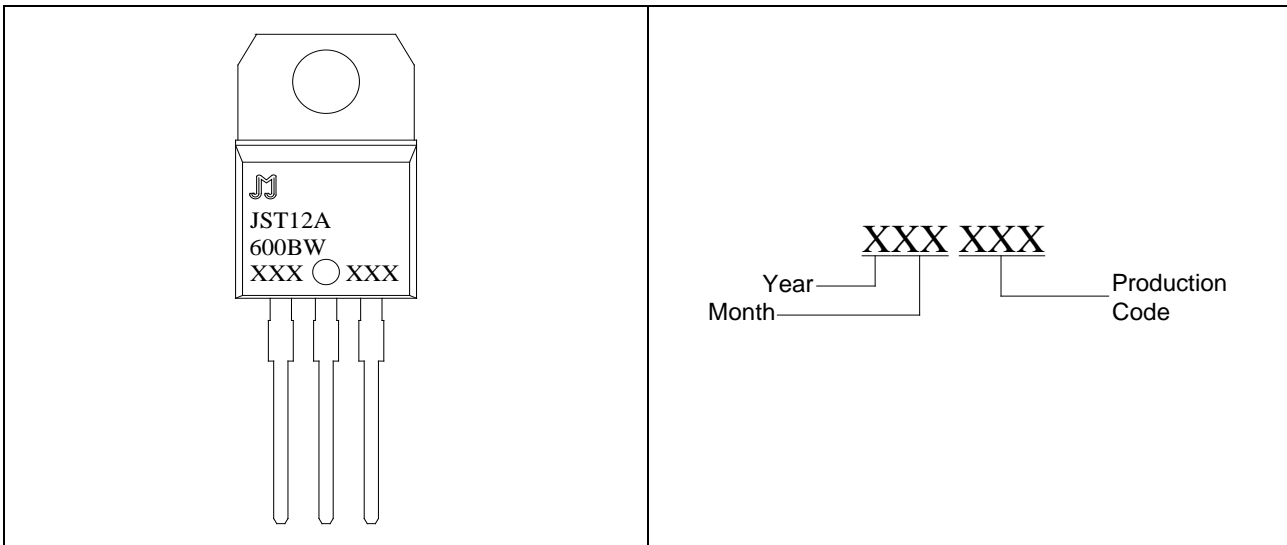
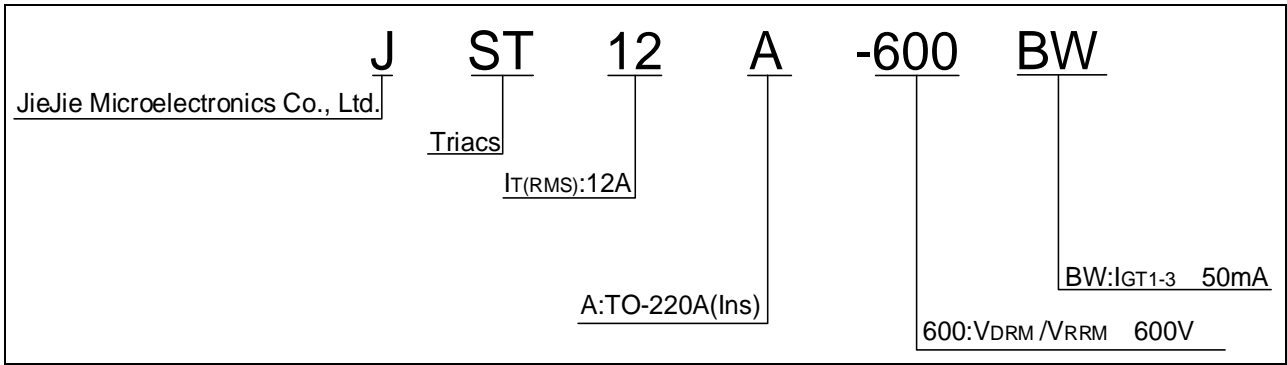
Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c = 86^\circ\text{C}$ )	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	120	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		132	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	72	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A/s}$
Peak gate current ( $t_p=20\text{ }\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W

Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	4.5	kV

( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	50	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				90	
$I_H$	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	2000	V s
(dI/dt)c	$j=125$		MIN.	20	A/ms
$t_{on}$	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	5	s
$t_{off}$				50	

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=17A t_p=380$ s	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.77	V
$R_D$	Dynamic resistance	$T_j=125$	35	
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$		

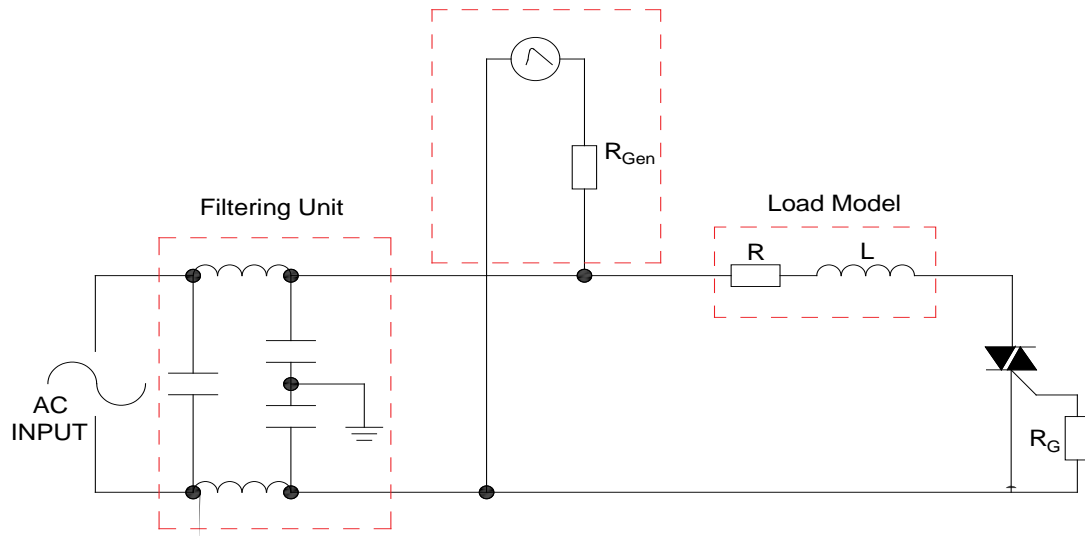


**FIG.1** Maximum power dissipation versus RMS on-state current

**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

IEC61000-4-5 Standards  
Surge Generator




Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
------------	----------------------------------	---------	---------	--------------------	------------------



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.